

MCM511000A•MCM51L1000A

AC OPERATING CONDITIONS AND CHARACTERISTICS ($V_{CC} = 5.0 \text{ V} \pm 10\%$, $T_A = 0 \text{ to } 70^\circ\text{C}$, Unless Otherwise Noted)

READ, WRITE, AND READ-MODIFY-WRITE CYCLES (See Notes 1, 2, 3, 4, and 5)

Parameter	Symbol		MCM511000A-70 MCM51L1000A-70		MCM511000A-80 MCM51L1000A-80		MCM511000A-10 MCM51L1000A-10		Unit	Notes
	Standard	Alternate	Min	Max	Min	Max	Min	Max		
Random Read or Write Cycle Time	t_{RELREL}	t_{RC}	130	—	150	—	180	—	ns	6
Read-Write Cycle Time	t_{RELREL}	t_{RWC}	155	—	175	—	210	—	ns	6
Page Mode Cycle Time	t_{CELCEL}	t_{PC}	40	—	45	—	55	—	ns	
Page Mode Read-Write Cycle Time	t_{CELCEL}	t_{PRWC}	65	—	70	—	85	—	ns	
Access Time from RAS	t_{RELQV}	t_{RAC}	—	70	—	80	—	100	ns	7, 8
Access Time from CAS	t_{CELOV}	t_{CAC}	—	20	—	20	—	25	ns	7, 9
Access Time from Column Address	t_{AVQV}	t_{AA}	—	35	—	40	—	50	ns	7, 10
Access Time from Precharge CAS	t_{CEHQV}	t_{CPA}	—	35	—	40	—	50	ns	7
CAS to Output in Low-Z	t_{CELOX}	t_{CLZ}	0	—	0	—	0	—	ns	7
Output Buffer and Turn-Off Delay	t_{CEHQZ}	t_{OFF}	0	20	0	20	0	20	ns	11
Transition Time (Rise and Fall)	t_T	t_T	3	50	3	50	3	50	ns	
RAS Precharge Time	t_{REHREL}	t_{RP}	50	—	60	—	70	—	ns	
RAS Pulse Width	t_{RELREH}	t_{RAS}	70	10,000	80	10,000	100	10,000	ns	
RAS Pulse Width (Fast Page Mode)	t_{RELREH}	t_{RASP}	70	100,000	80	100,000	100	100,000	ns	
RAS Hold Time	t_{CELREH}	t_{RSH}	20	—	20	—	25	—	ns	
CAS Hold Time	$t_{RELC EH}$	t_{CSH}	70	—	80	—	100	—	ns	
CAS Pulse Width	t_{CELCEH}	t_{CAS}	20	10,000	20	10,000	25	10,000	ns	
RAS to CAS Delay Time	t_{RELCEL}	t_{RCD}	20	50	20	60	25	75	ns	12
RAS to Column Address Delay Time	t_{RELAV}	t_{RAD}	15	35	15	40	20	50	ns	13
CAS to RAS Precharge Time	t_{CEHREL}	t_{CRP}	5	—	5	—	5	—	ns	
CAS Precharge Time (Page Mode Cycle Only)	t_{CEHCEL}	t_{CP}	10	—	10	—	10	—	ns	
Row Address Setup Time	t_{AVREL}	t_{ASR}	0	—	0	—	0	—	ns	
Row Address Hold Time	t_{RELAX}	t_{RAH}	10	—	10	—	15	—	ns	
Column Address Setup Time	t_{AVCEL}	t_{ASC}	0	—	0	—	0	—	ns	
Column Address Hold Time	t_{CELAX}	t_{CAH}	15	—	15	—	20	—	ns	
Column Address Hold Time Referenced to RAS	t_{RELAX}	t_{AR}	55	—	60	—	75	—	ns	
Column Address to RAS Lead Time	t_{AVREH}	t_{RAL}	35	—	40	—	50	—	ns	

(continued)

NOTES:

- V_{IH} min and V_{IL} max are reference levels for measuring timing of input signals. Transition times are measured between V_{IH} and V_{IL} .
- An initial pause of 200 μs is required after power-up followed by 8 RAS cycles before proper device operation is guaranteed.
- The transition time specification applies for all input signals. In addition to meeting the transition rate specification, all input signals must transmit between V_{IH} and V_{IL} (or between V_{IL} and V_{IH}) in a monotonic manner.
- AC measurements $t_T = 5.0 \text{ ns}$.
- TF pin must be at V_{IL} or open if not used.
- The specifications for t_{RC} (min) and t_{RWC} (min) are used only to indicate cycle time at which proper operation over the full temperature range ($0^\circ\text{C} \leq T_A \leq 70^\circ\text{C}$) is assured.
- Measured with a current load equivalent to 2 TTL ($-200 \mu\text{A}$, $+4 \text{ mA}$) loads and 100 pF with the data output trip points set at $V_{OH} = 2.0 \text{ V}$ and $V_{OL} = 0.8 \text{ V}$.
- Assumes that $t_{RCD} \leq t_{RC}$ (max).
- Assumes that $t_{RCD} \geq t_{RC}$ (max).
- Assumes that $t_{RAD} \geq t_{RAD}$ (max).
- t_{OFF} (max) defines the time at which the output achieves the open circuit condition and is not referenced to output voltage levels.
- Operation within the t_{RCD} (max) limit ensures that t_{RAC} (max) can be met. t_{RCD} (max) is specified as a reference point only; if t_{RCD} is greater than the specified t_{RCD} (max) limit, then access time is controlled exclusively by t_{CAC} .
- Operation within the t_{RAD} (max) limit ensures that t_{RAC} (max) can be met. t_{RAD} (max) is specified as a reference point only; if t_{RAD} is greater than the specified t_{RAD} (max), then access time is controlled exclusively by t_{AA} .